

Amendments to the Specification

Please add the following Abstract on a separate page.

ABSTRACT

[0001] A method for reworking semiconductor materials includes: (i) applying a silicone composition to a surface of a substrate to form a film, (ii) exposing a portion of the film to radiation to produce a partially exposed film having non-exposed regions covering a portion of the surface and exposed regions covering the remainder of the surface; (iii) heating the partially exposed film for an amount of time such that the exposed regions are substantially insoluble in a developing solvent and the non-exposed regions are soluble in the developing solvent; (iv) removing the non-exposed regions of the heated film with the developing solvent to form a patterned film; (v) heating the patterned film for an amount of time sufficient to form a cured silicone layer; and (vi) removing all or a portion of the cured silicone layer by exposure to an anhydrous etching solution including an organic solvent and a base.